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Type: **Poster Presentation**

The Infrared Plasma Resonance of P in SiC

Wednesday, 13 July 2011 17:00 (2 hours)

The concentration of any dopant in a semiconductor can usually easily and readily be established using the plasma resonance minimum. Infrared reflectance spectroscopy was used to assess the doping of SiC wafers by phosphor implantation. However, results obtained did not match the theoretical predictions. The problem was investigated, including an assessment of the applicable theory. Results will be presented and discussed.

**Level (Hons, MSc,
 PhD, other)?**

other

**Consider for a student
 award (Yes / No)?**

No

**Would you like to
 submit a short paper
 for the Conference
 Proceedings (Yes / No)?**

No

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